

Ba₄AgGa₅Pn₈ (n=P, As): New Pnictide-Based Compounds with Nonlinear Optical Potential

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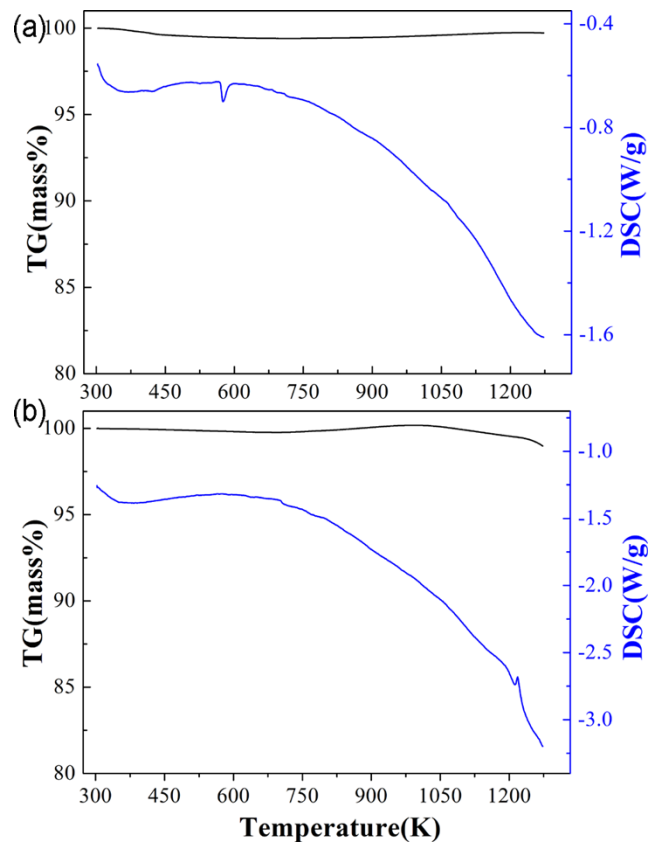


Figure S1. TG-DSC measurements on (a) $\text{Ba}_4\text{AgGa}_5\text{P}_8$ and (b) $\text{Ba}_4\text{AgGa}_5\text{As}_8$, conducted in an inert atmosphere of argon.

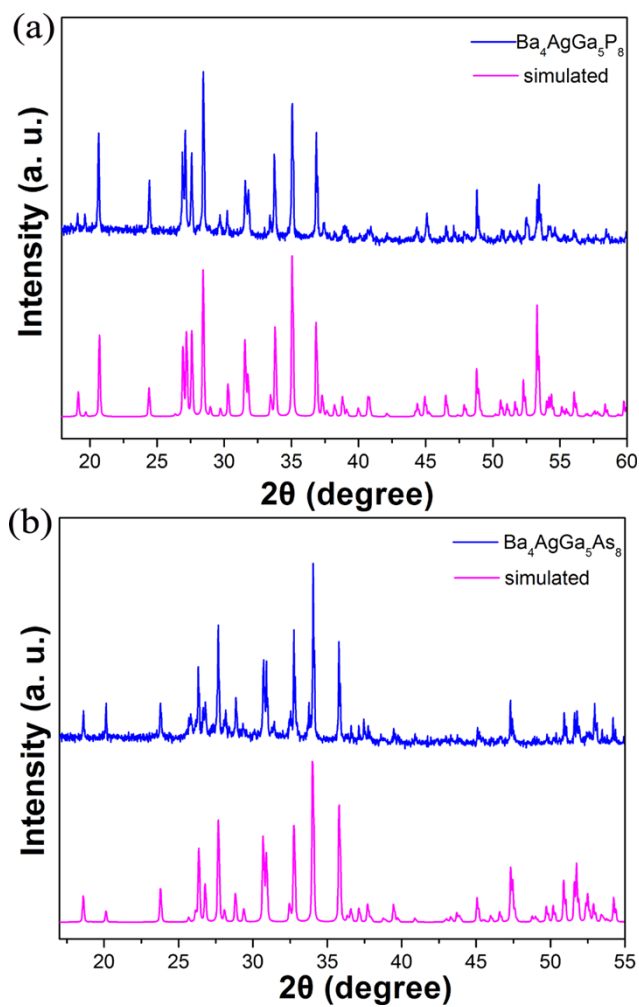


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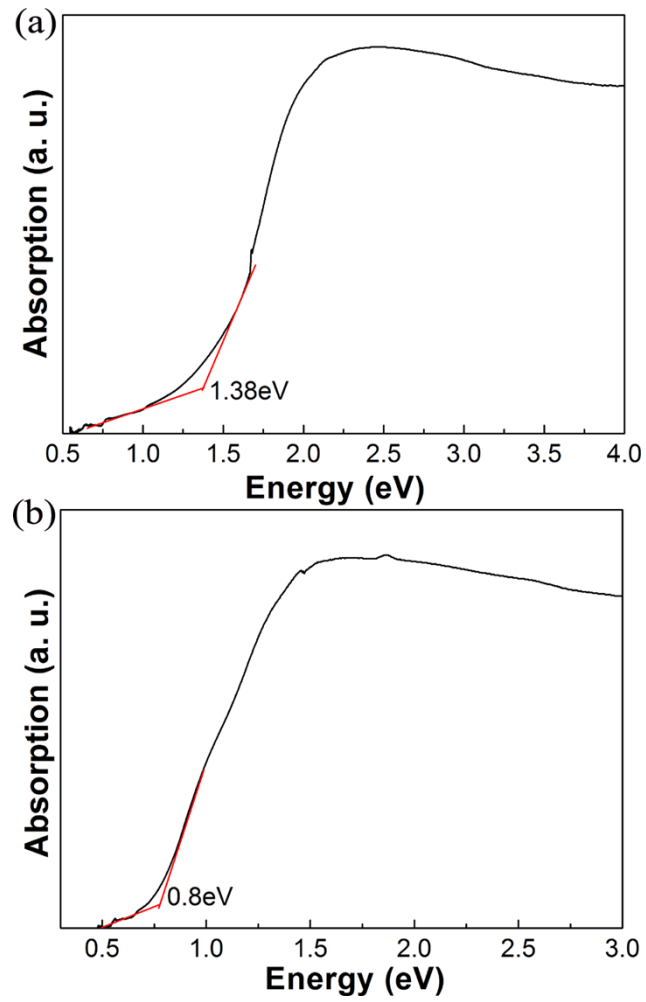


Figure S3. Optical absorption spectra measured on the polycrystalline samples of (a) $\text{Ba}_4\text{AgGa}_5\text{P}_8$ and (b) $\text{Ba}_4\text{AgGa}_5\text{As}_8$.

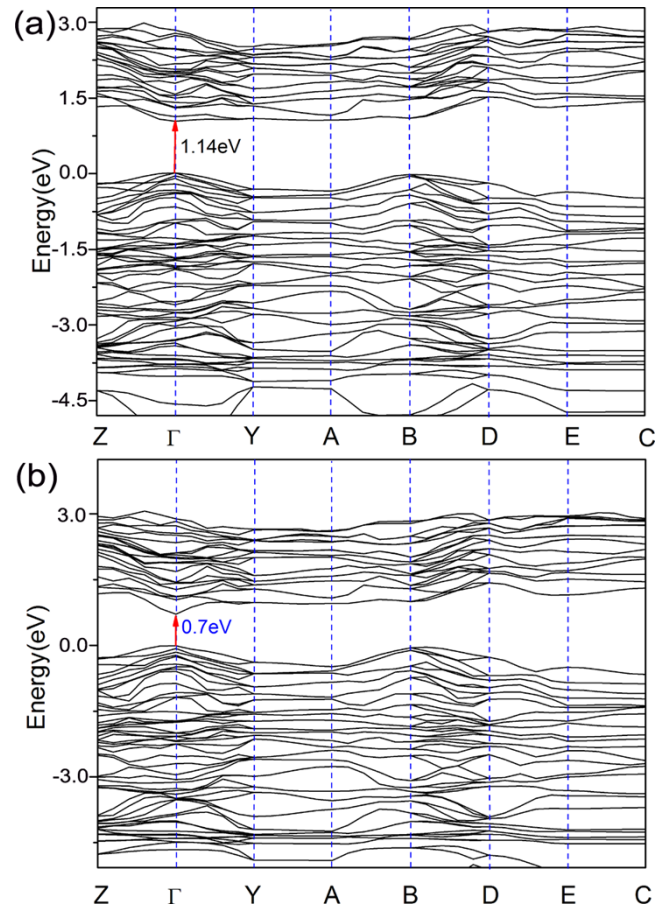


Figure S4. Electronic band structures calculated on (a) $\text{Ba}_4\text{AgGa}_5\text{P}_8$ and (b) $\text{Ba}_4\text{AgGa}_5\text{As}_8$.

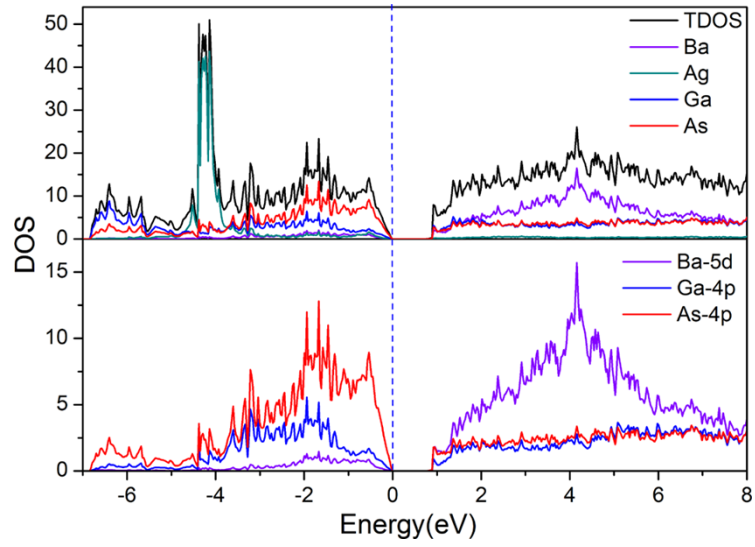


Figure S5. Calculated total DOS and projected DOS for $\text{Ba}_4\text{AgGa}_5\text{As}_8$. The dotted line marked the Fermi level.

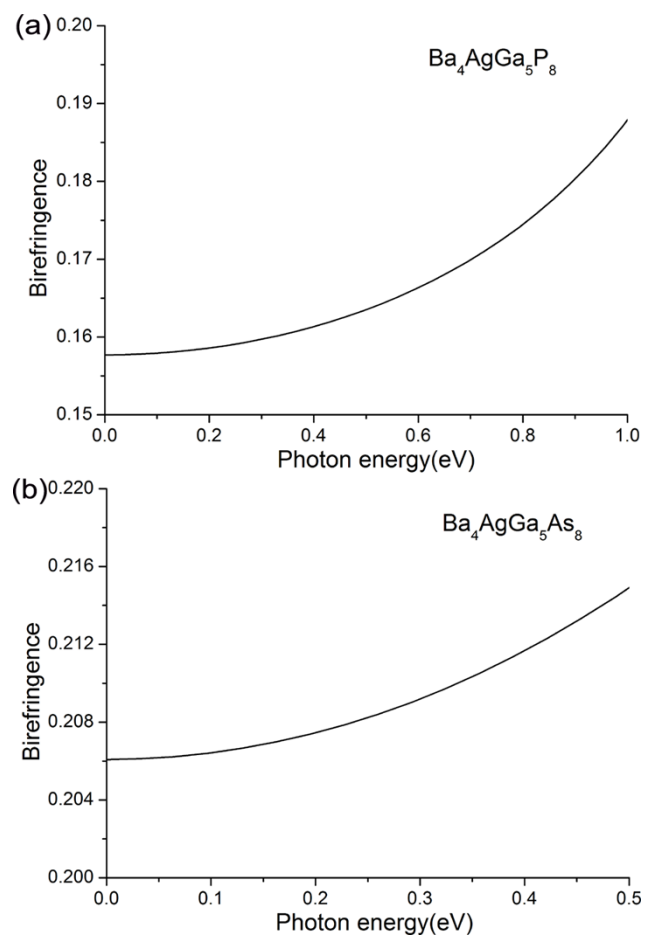


Figure S6. The calculated birefringence (Δn) for (a) $\text{Ba}_4\text{AgGa}_5\text{P}_8$ and (b) $\text{Ba}_4\text{AgGa}_5\text{As}_8$.

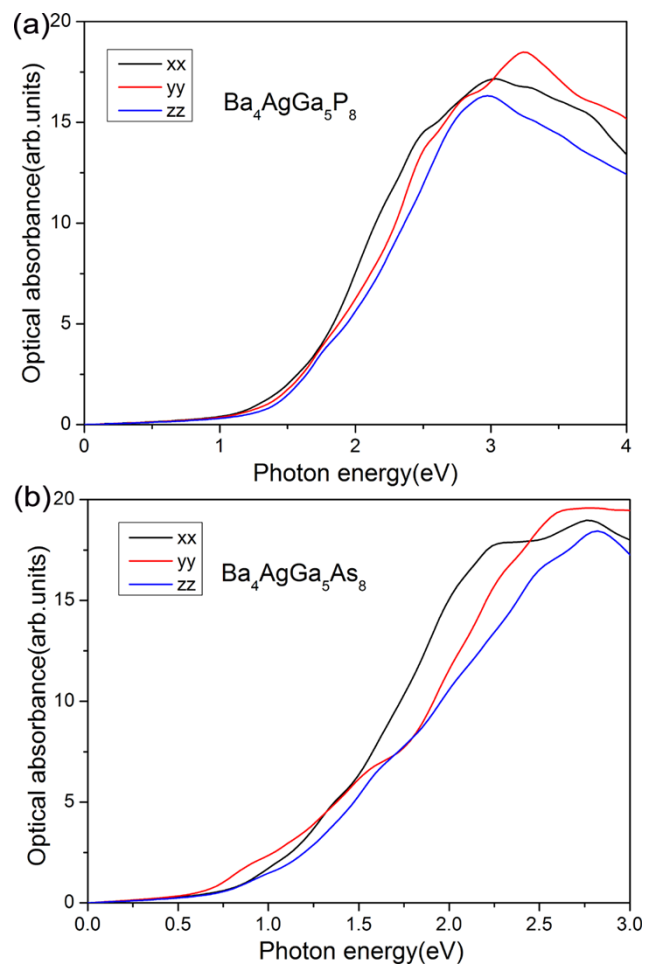


Figure S7. Calculated absorption coefficients of (a) $\text{Ba}_4\text{AgGa}_5\text{P}_8$ and (b) $\text{Ba}_4\text{AgGa}_5\text{As}_8$.

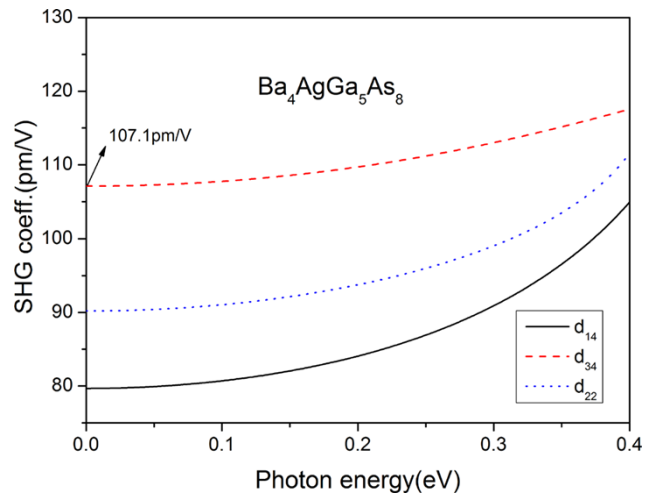


Figure S8. Calculated frequency-dependent second harmonic generation coefficients for $\text{Ba}_4\text{AgGa}_5\text{As}_8$.

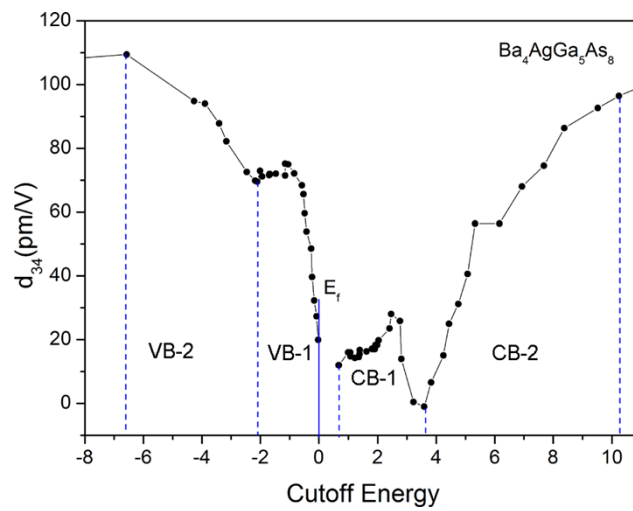


Figure S9. Cutoff-energy-depending static SHG coefficients for $\text{Ba}_4\text{AgGa}_5\text{As}_8$. The dotted lines mark the different regions in VB and CB.

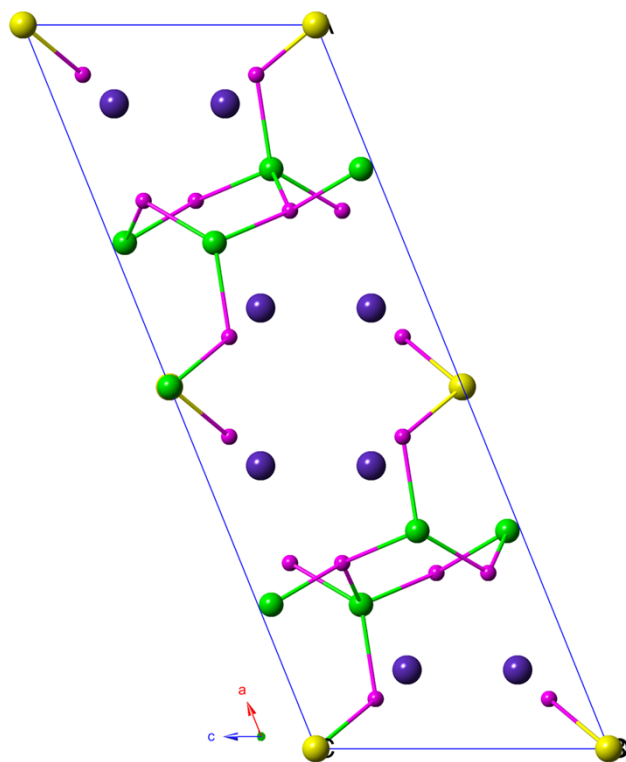


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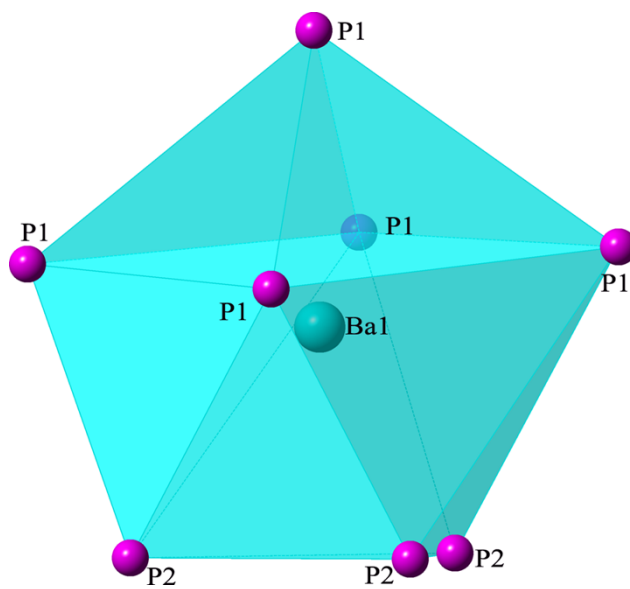


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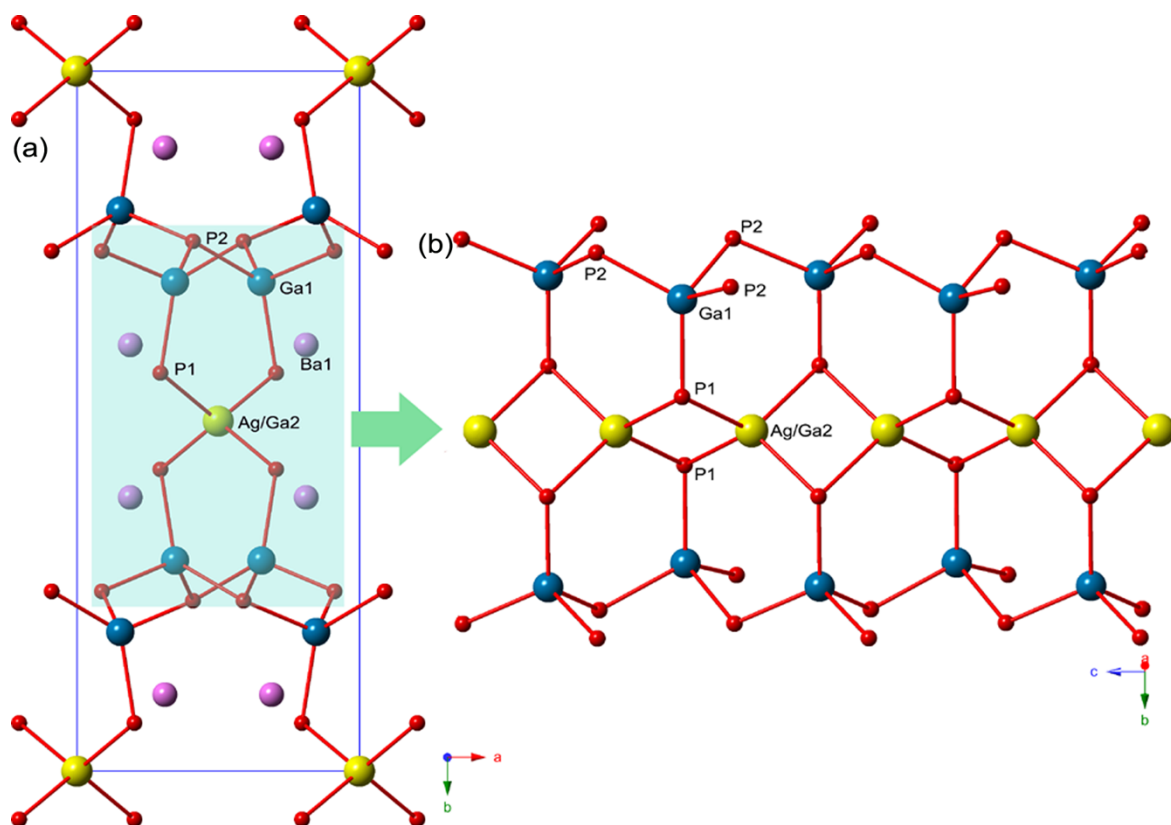


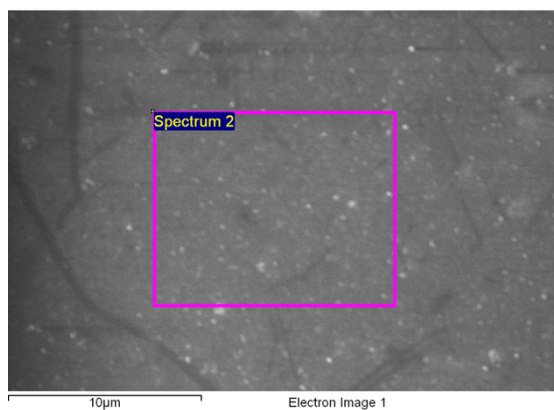
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13. EDX analyses on the composition of a single crystal for (a) Ba₄AgGa₅P₈ and (b) Ba₄AgGa₅As₈.

(a) Ba₄AgGa₅P₈

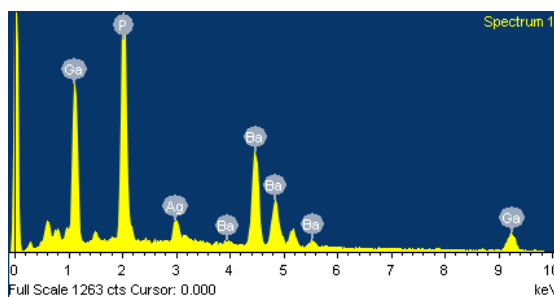
Point 1

Element	Weight%	Atomic%	Composition
P K	21.68	47.36	8.54
Ga L	27.90	27.07	4.88
Ag L	5.41	3.40	0.61
Ba L	45.01	22.18	4



Point 2

Element	Weight%	Atomic%	Composition
P K	21.89	47.54	8.76
Ga L	28.43	27.43	5.05
Ag L	5.34	3.33	0.61
Ba L	44.33	21.71	4

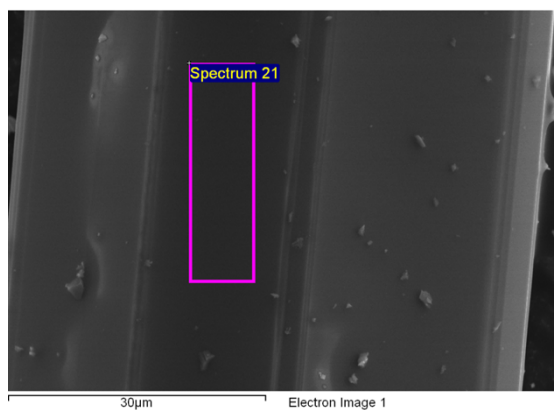


Averaged Composition: Ba₄Ag_{0.61}Ga_{4.97}P_{8.65}

(b) Ba₄AgGa₅As₈

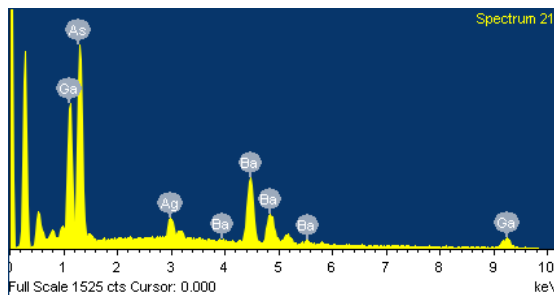
Point 1

Element	Weight%	Atomic%	Composition
As L	36.32	43.33	7.56
Ga L	22.43	28.76	5.02
Ag L	6.02	4.99	0.87
Ba L	35.23	22.93	4



Point 2

Element	Weight%	Atomic%	Composition
As L	36.46	43.39	7.70
Ga L	22.65	28.97	5.14
Ag L	6.18	5.11	0.91
Ba L	34.70	22.53	4



Averaged Composition: Ba₄Ag_{0.89}Ga_{5.08}As_{7.63}

Table S1. Refined atomic coordinates and isotropic displacement parameters for two polymorphs of $\text{Ba}_4\text{AgGa}_5\text{Pn}_8$ (Pn=P, As).

<i>Atoms</i>	<i>Wyckoff site</i>	<i>x</i>	<i>y</i>	<i>z</i>	<i>U_{eq} (Å²)</i>
$\text{Ba}_4\text{AgGa}_5\text{P}_8$					
Ba1	8(<i>c</i>)	0.81096(10)	0.60903(4)	0.7542(2)	0.0204(2)
Ga1	8(<i>c</i>)	0.84356(15)	0.80091(6)	0.7492(4)	0.0088(3)
Ag/Ga2 ^{<i>b</i>}	4(<i>a</i>)	1	1	1	0.0190(4)
P1	8(<i>c</i>)	0.7961(4)	0.93114(16)	0.7481(13)	0.0210(7)
P2	8(<i>c</i>)	0.5889(5)	0.7568(2)	0.9334(6)	0.0121(7)
$\text{Ba}_4\text{AgGa}_5\text{As}_8$					
Ba1	8(<i>c</i>)	0.80368(4)	0.61010(2)	0.75587(6)	0.01815(12)
Ga1	8(<i>c</i>)	0.84459(7)	0.80115(3)	0.74621 (13)	0.01073(14)
Ag/Ga2 ^{<i>b</i>}	4(<i>a</i>)	1	1	1	0.01522(17)
As1	8(<i>c</i>)	0.79006(8)	0.93160(3)	0.74750(15)	0.02013(16)
As2	8(<i>c</i>)	0.58454(8)	0.75922(3)	0.93462(10)	0.01127(15)

^{*a*} U_{eq} is defined as one third of the trace of the orthogonalized U^{ij} tensor.

^{*b*}Ag or Ga2 occupancy are both constrained to 50% at the mixing sites.

Table S2. The selected important interatomic distances (Å) in Ba₄AgGa₅Pn₈ (Pn=P, As).

Atom pairs	Distances (Å)	Atom pairs	Distances (Å)
Ba ₄ AgGa ₅ P ₈			
Ba1– P1	3.301(5)	Ga1 – P1	2.376(4)
P1	3.409 (9)	P2	2.365(5)
P1	3.485(9)	P2	2.371(4)
P1	3.612 (5)	P2	2.380(4)
P2	3.287(5)	Ag/Ga2– P1 × 2	2.529(7)
P2	3.331(5)	P1 × 2	2.546(6)
P2	3.367(4)		
Ba ₄ AgGa ₅ As ₈			
Ba1– As1	3.3896(7)	Ga1– As 1	2.4575(8)
As1	3.4833(11)	As 2	2.4441(10)
As1	3.5914(11)	As 2	2.4514(9)
As1	3.7187(7)	As 2	2.4694(9)
As2	3.3625(8)	Ag/Ga2– As 1 × 2	2.6223(10)
As2	3.4297(7)	As 1 × 2	2.6440(10)
As2	3.4377(7)		